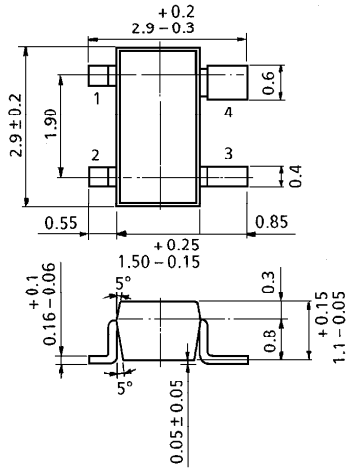
TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS319

LOW VOLTAGE HIGH SPEED SWITCHING.

Unit in mm

- Low Forward Voltage : $V_{F(3)}$=0.54V (Typ.)
- Low Reverse Current : I_R=5μA (Max.)
- Small Package : SC-61



MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Maximum (Peak) Forward Current	I_{FM}	300 (*)	mA
Average Forward Current	I_O	100 (*)	mA
Power Dissipation	P	150 (*)	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	−55~125	°C

JEDEC	—
EIAJ	SC-61
TOSHIBA	2-3J1A

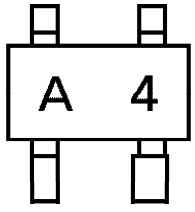
Weight : 0.013g

(*) Unit Rating. Total Rating=Unit Rating×1.5.

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_{F(1)}$	I_F=1mA	—	0.28	—	V
	$V_{F(2)}$	I_F=10mA	—	0.36	—	
	$V_{F(3)}$	I_F=100mA	—	0.54	0.60	
Reverse Current	I_R	V_R=40V	—	—	5	μA
Total Capacitance	C_T	V_R=0, f=1MHz	—	18	25	pF

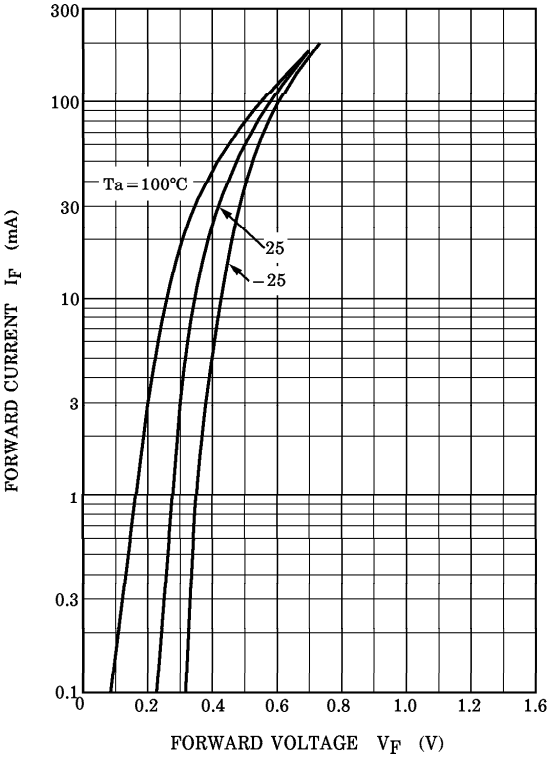
MARKING



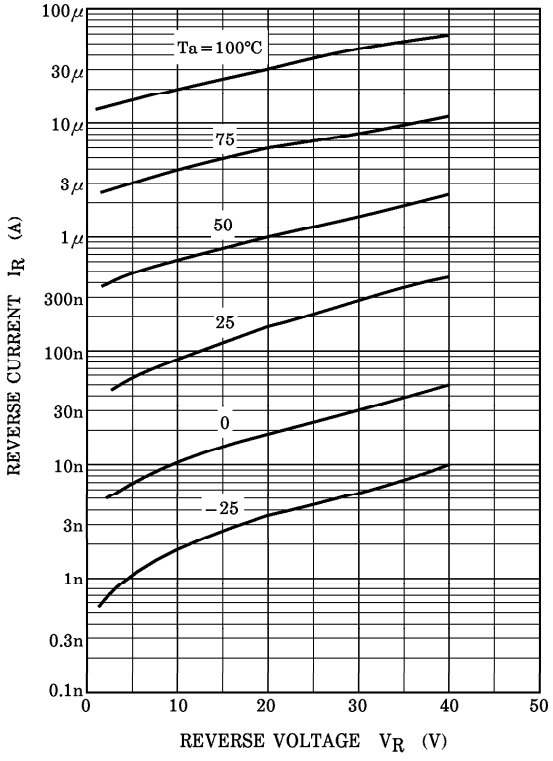
961001EAA2

,

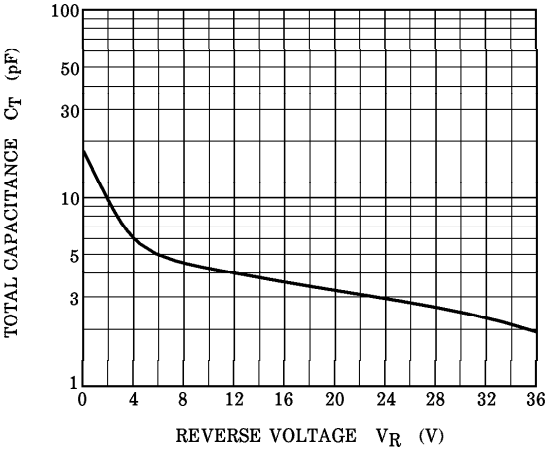
$I_F - V_F$



$I_R - V_R$



$C_T - V_R$



961001EAA2'